

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Previously Presented) A semiconductor device comprising:
 - a plurality of conductive paths electrically separated from one another by a trench;
 - a first conductive path of said plurality of conductive paths, having a die pad shape;
 - a semiconductor chip disposed on said first conductive path; said first conductive path coupled to said semiconductor chip through a thermally conductive material;
 - a second conductive path disposed peripherally around said semiconductor chip, having a bonding pad shape;
 - a third conductive path having a shape of an external connecting pad and coupled to said second conductive path, said third conductive path being disposed underneath said semiconductor chip and coupled to said semiconductor chip through an insulating material;
 - connecting means for electrically connecting said semiconductor chip to said second conductive path;
 - insulating resin covering said semiconductor chip, filling in the trench, and integrally supporting the semiconductor chip and the conductive paths with a bottom surface of the paths exposed.
2. (Previously Presented) A semiconductor device according to claim 1 wherein said first conductive path has a smaller size than that of the rear surface of said semiconductor chip, said third conductive path has a larger size than that of said second conductive path.

3. (Original) A semiconductor device according to claim 1 wherein said first conductive path is provided on the rear surface of said semiconductor chip to have a smaller size than that of said semiconductor chip;

said second conductive path is provided in plurality outside said semiconductor chip, one of said plurality of the second conductive paths being formed in the form of an island and another thereof being formed integrally to a wiring extended to the rear face of said semiconductor chip, and

said wiring is formed integrally to a third conductive path having a shape of an external connecting pad provided between the periphery of said semiconductor chip and said first conductive path.

4. (Previously Canceled)

5. (Previously Presented) A semiconductor device according to claim 2, wherein the insulating material is provided between said wiring extended to the rear surface of said semiconductor chip and said semiconductor chip or between said third conductive path and said semiconductor chip.

6. (Original) A semiconductor device according to claim 1 , wherein an insulating material is provided over the entire region of a rear surface of said semiconductor chip.

7. (Original) A semiconductor device according to claim 1, wherein said connecting means is a metallic wire.

8. (Previously Presented) A semiconductor device according to claim 1, wherein the side of each of said conductive paths is curved to mate with said insulating resin.

9. (Original) A semiconductor device according to of claim 1 , wherein said conductive paths are made of a conductive foil selected from the group consisting of copper, aluminum and iron-nickel.

10. (Original) A semiconductor device according to of claim 1 , wherein the upper surface of said conductive paths is covered with a metallic material different from that of said conductive paths.

11. (Previously Presented) A semiconductor device according to claim 10, further comprising a conductive film selectively covering said conductive paths and having made of material selected from the group consisting of nickel, silver and gold.

12. (Previously Presented) A semiconductor device according to claim 1, wherein said first conductive path is coupled with a conductive pattern formed on a mounting board through a thermally conductive material.

13. (Original) A semiconductor device according to claim 3, wherein said second conductive path which is formed in an island is a test pin.

14. (Previously Presented) A semiconductor device comprising:
a plurality of conductive paths electrically separated from one another by a trench;
a semiconductor chip connected with at least one of said conductive paths through a thermal conductive material; and
insulating resin which covers said semiconductor chip, is embedded in the trench among said plurality of conductive paths and integrally supports the conductive paths, rear surface of which are at least partially exposed from the insulating resin,

wherein at least another one of said conductive paths is disposed at a periphery of said semiconductor chip and extends underneath the chip and coupled to the chip through an insulating material to form an external terminal.

15. (Original) A semiconductor device according to claim 14, wherein said semiconductor chip is connected with said conductive path through bonding wire.

16. (Original) A semiconductor device according to claim 14, wherein said semiconductor chip is directly connected with said conductive path.

17. (Currently Amended) A semiconductor device comprising:

a semiconductor chip; and

a plurality of conductive paths electrically separated by a trench, the conductive paths comprising a die pad shaped conductive path disposed below and substantially at the center of the semiconductor chip, an external connecting shaped conductive path disposed below the semiconductor chip, and a bonding pad shaped conductive path disposed beyond the semiconductor chip and being connected to ~~the conductive path of the external connecting shaped conductive path~~;

wherein the semiconductor chip is disposed over and coupled to the die pad shaped conductive path ~~of the die pad shape~~ through a thermally conductive material, and the external connection shaped conductive path ~~of the external connection shape~~ is coupled to said semiconductor chip through an insulating material.

18. (Currently Amended) A semiconductor device according to claim 17, further comprising:

connecting means for electrically connecting said semiconductor chip to the bonding pad shaped conductive path ~~of the bonding pad shape~~;

19. (New) A semiconductor device according to claim 17, further comprising:
an insulating resin covering said semiconductor chip, filling in the trench, and integrally supporting the semiconductor chip and the conductive paths with a bottom surface of the paths exposed.

20. (Currently Amended) A semiconductor device according to claim 17 wherein the the die pad shaped conductive path ~~of the die pad shape~~ has a smaller size than that that of the rear surface of said semiconductor chip, the external connecting shaped conductive path ~~of the external connecting shape~~ is larger than the bonding pad shaped conductive path ~~of the bonding pad shape~~.

21. (Currently Amended) A semiconductor device according to claim 20, wherein the insulating material is provided between said wiring extended to the rear surface of said semiconductor chip and said semiconductor chip or between the external connecting shaped conductive path ~~of the external connecting shape~~ and said semiconductor chip.

22. (Previously Added) A semiconductor device according to claim 17, wherein the side of each of said conductive paths is curved to mate with said insulating resin.

23. (Previously Presented) A semiconductor device according to claim 17, further comprising:

a conductive film selectively covering said conductive paths and having made of material selected from the group consisting of nickel, silver and gold.

24. (Currently Amended) A semiconductor device according to claim 17, wherein the die pad shaped conductive path ~~of the die pad shape~~ is coupled with a conductive pattern formed on a mounting board through a thermally conductive material.

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25. (Canceled)